

Fast switching diode chip in EMCON 3-Technology

FEATURES:

- 600V EMCON 3 technology 70 μm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

- power module
- discrete components



Applications:

• drives

Chip Type	V_R	I _F	Die Size	Package
SIDC20D60C6	600V	75A	5.37 x 3.75 mm ²	sawn on foil

MECHANICAL PARAMETER:

MECHANICAL PARAMETER:	1				
Raster size	5.37 x 3.75				
Area total / active	20.14 / 16.66	mm ²			
Anode pad size	4.67 x 3.05				
Thickness	70	μm			
Wafer size	150	mm			
Flat position	180	deg			
Max. possible chips per wafer	701 pcs				
Passivation frontside	Photoimide				
Anode metallization	e metallization 3200 nm AlSiCu				
Cathode metallization	Ni Ag -system suitable for epoxy and soft solder die bonding				
Die bond	electrically conductive glue or solder				
Wire bond	AI, ≤500μm				
Reject ink dot size	Ø 0.65mm; max 1.2mm				
Recommended storage environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C				



Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		600	V
Continuous forward current limited by	1_		1)	- A
T _{jmax}	I _F			
Maximum repetitive forward current	1		150	
limited by T _{jmax}	/ FRM		130	
Operating junction and storage temperature	$T_{\rm j}$, $T_{ m stg}$		-40+175	°C

¹⁾ depending on thermal properties of assembly

Static Electrical Characteristics (tested on chip), $T_{\rm j}$ =25 °C, unless otherwise specified

Parameter	Symbol	Cond	Value			Unit	
raiailletei	Syllibol	Conditions		min.	Тур.	max.	T OILL
Reverse leakage current	I _R	V _R = 600 V	<i>T_j</i> =25° <i>C</i>			27	μΑ
Cathode-Anode breakdown Voltage	V _{Br}	I _R = 0.25mA	$T_j=25^{\circ}C$	600			V
Forward voltage drop	V_{F}	I _F = 75A	$T_j=25^{\circ}C$	1.2	1.6	1.9	٧

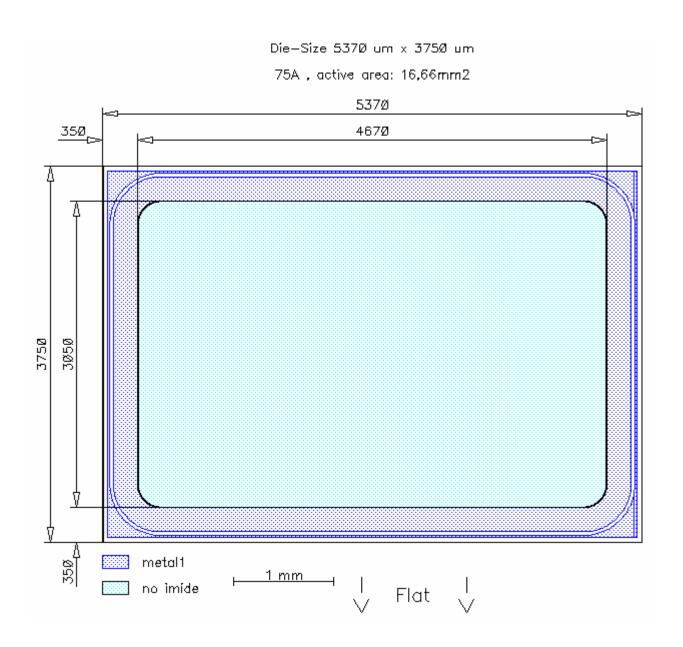
Dynamic Electrical Characteristics (verified by design/characterization), inductive load

Parameter	Symbol	Conditions		Value 2)			Unit
raiaillelei	Syllibol			min.	Тур.	max.	7 01111
Peak reverse recovery current	I _{RM}	$I_F=75A$ $di/dt=4000A/\mu s$ $V_R=300V$ $V_{GE}=-15V$	$T_j = 25 ^{\circ}C$ $T_j = 125 ^{\circ}C$ $T_j = 150 ^{\circ}C$		100 115 125		A
Recovered charge	Q _r	$I_F=75A$ $di/dt=4000A/\mu s$ $V_R=300V$ $V_{GE}=-15V$	$T_j = 25 \text{ °C}$ $T_j = 125 \text{ °C}$ $T_j = 150 \text{ °C}$		3.00 6.00 7.50		μC
Reverse recovery energy	E _{rec}	$I_F=75A$ $di/dt=4000A/\mu s$ $V_R=300V$ $V_{GE}=-15V$	$T_j = 25 ^{\circ}C$ $T_j = 125 ^{\circ}C$ $T_j = 150 ^{\circ}C$		0.95 1.50 1.85		mJ

²⁾ values also influenced by parasitic L- and C- in measurement and package.



CHIP DRAWING:





This chip data sheet refers to the device data sheet Description: AQL 0,65 for visual inspection according to failure catalog Electrostatic Discharge Sensitive Device according to MIL-STD 883 Test-Normen Villach/Prüffeld

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